

ABSTRACT

Multilayer photoresist systems are provided . In particular aspects, the invention relates to underlayer composition for an overcoated photoresist, particularly an overcoated silicon-containing photoresist. Preferred underlayer compositions comprise
5 one or more resins or other components that impart etch-resistant and antireflective properties, such as one or more resins that contain phenyl or other etch-resistant groups and anthracene or other moieties that are effective anti-reflective chromophores for photoresist exposure radiation.